P-Channel 200-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

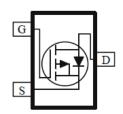
Typical Applications:

- PoE Power Sourcing Equipment
- PoE Powered Devices
- Telecom DC/DC converters
- White LED boost converters

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(\Omega)$	I⊳(A)	
-200	2.5 @ V _{GS} = -10V	-0.6	
	2.8 @ V _{GS} = -5.5V	-0.5	
	2.6 @ V _{GS} – -5.5V	-0.5	







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage			-200	V	
Gate-Source Voltage	V_{GS}	±20	V		
Continuos Durin Commenta	T _A =25°C	;	-0.6		
Continuous Drain Current ^a	T _A =70°C	' D	-0.5	Α	
Pulsed Drain Current ^b	I _{DM}	5			
Continuous Source Current (Diode Conduction) ^a		Is	1.2	Α	
Device Dissipation 8	T _A =25°C	P _D	1.3	W	
Power Dissipation ^a	T _A =70°C		0.8	٧٧	
Operating Junction and Storage Temperature Range			-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	100	°C/W		
Maximum Junction-to-Ambient	Steady State	I V ₀ JA	166	C/VV		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

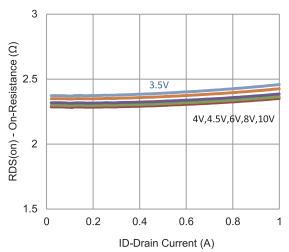
MI2351P

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current		$V_{DS} = -160 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA
	DSS	$V_{DS} = -160 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	
On-State Drain Current	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-0.5			Α
Drain-Source On-Resistance	r	$V_{GS} = -10 \text{ V}, I_{D} = -0.5 \text{ A}$			2.5	Ω
Dialii-Source Oil-Nesistance	r _{DS(on)}	$V_{GS} = -5.5 \text{ V}, I_D = -0.4 \text{ A}$			2.8	
Forward Transconductance	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -0.5 \text{ A}$		1.8		S
Diode Forward Voltage	V_{SD}	$I_{S} = -0.6 \text{ A}, V_{GS} = 0 \text{ V}$		-0.87		V
		Dynamic				
Total Gate Charge	Q_g	$V_{DS} = -100 \text{ V}, V_{GS} = -5.5 \text{ V},$		3.7		nC
Gate-Source Charge	Q_{gs}	$I_{D} = -0.5A$		1.1		
Gate-Drain Charge	Q_{gd}	ID = -0.574		1.5		
Turn-On Delay Time	t _{d(on)}	$V_{DD} = -100 \text{ V}, R_{L} = 200 \Omega,$		4		
Rise Time	t _r	$I_{D} = -0.5A,$		10		no
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		13		ns
Fall-Time	t _f	V GEN10 V, T GEN - 0 12		10		
Input Capacitance	C _{iss}			301		
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		39		pF
Reverse Transfer Capacitance	C _{rss}]		21		

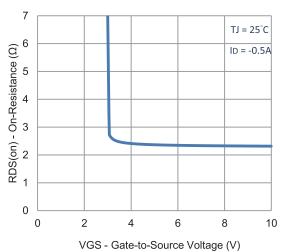
Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

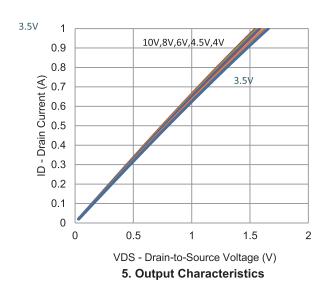
Typical Electrical Characteristics

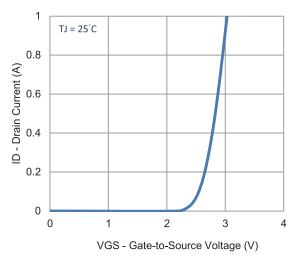


1. On-Resistance vs. Drain Current

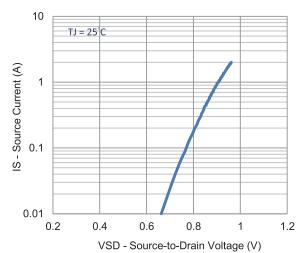


3. On-Resistance vs. Gate-to-Source Voltage

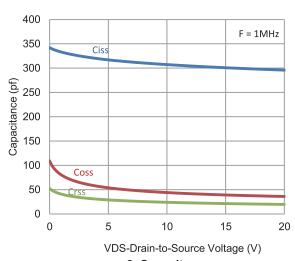




2. Transfer Characteristics



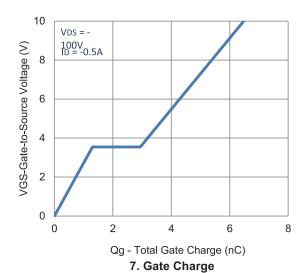
4. Drain-to-Source Forward Voltage



6. Capacitance

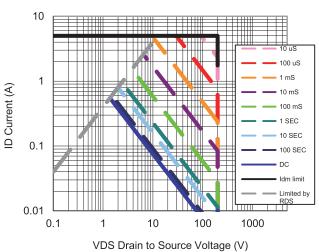


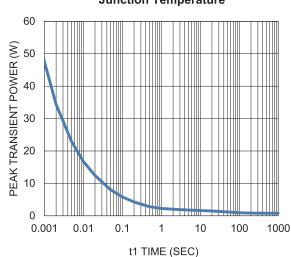
2



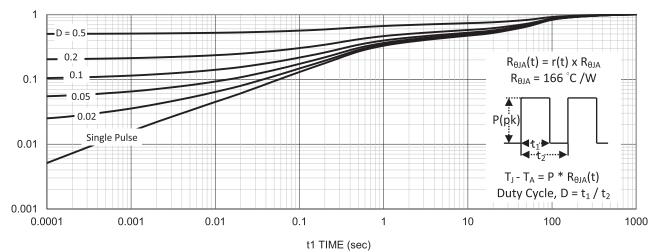
0.5 -50 -25 0 25 50 75 100 125 150 TJ - Junction Temperature (°C)

8. Normalized On-Resistance Vs Junction Temperature





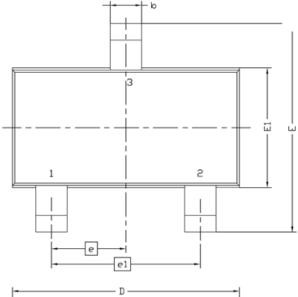
9. Safe Operating Area 10. Single Pulse Maximum Power Dissipation



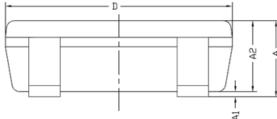
11. Normalized Thermal Transient Junction to Ambient

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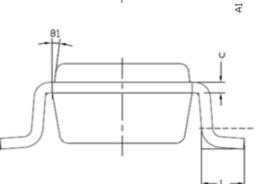
Package Information

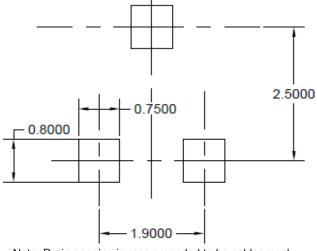


Symbol	MILLIMETERS		
Syllibol	MIN	MAX	
Α	0.8	1.2	
A1	0	0.1	
A2	0.7	1.1	
b	0.3	0.5	
С	0.1	0.2	
D	2.7	3.1	
Е	2.6	3	
E1	1.4	1.8	
е	0.95 BSC		
e1	1.9 BSC		
Ĺ	0.3	0.6	
θ1	7° NOM		



Recommended Pad Layout





Note: Drain opening is recommended to be solder mask defined in a copper fill for improved thermal performance

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